

Supporting information

***N*-type Ohmic contact and *p*-type Schottky contact of monolayer InSe transistors**

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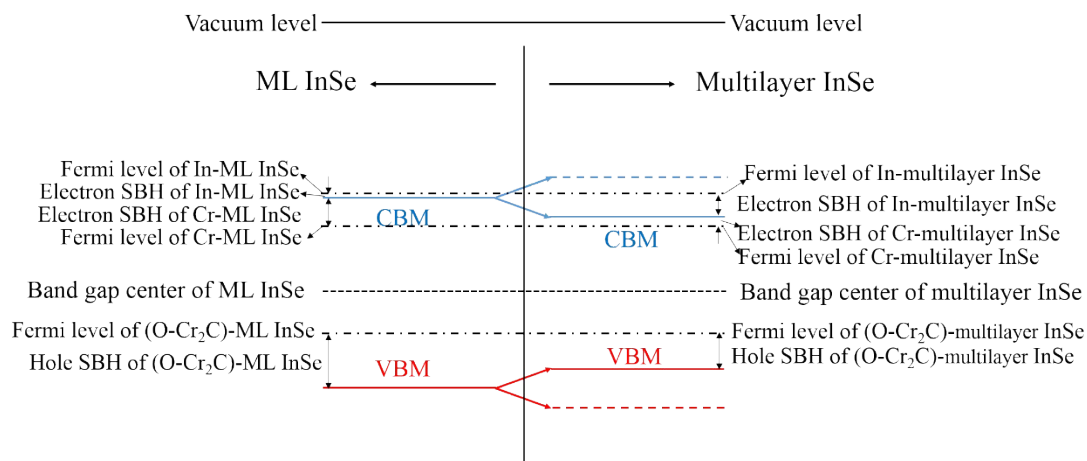


Figure S1. A schematic illustration of the SBH evolution from ML InSe to multilayer InSe. The CBM/VBM of ML InSe is split when forming multilayer InSe. There is consistent polarity and relative relation of the SBH between ML and multilayer InSe.